

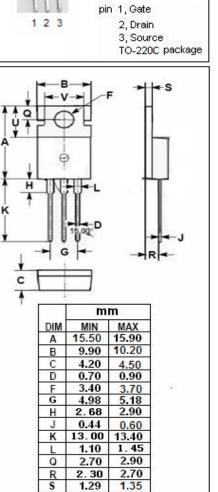
### **INCHANGE SEMICONDUCTOR**

# isc P-Channel MOSFET Transistor

### **IXTP28P065T**

• FEATU	IRES			2
<ul> <li>Static c</li> </ul>	drain-source on-resistance:			
RDS(	on)≪45mΩ			
<ul> <li>100% avalanche tested</li> </ul>				
	Im Lot-to-Lot variations for robust dev	vice		s I F T
perform	nance and reliable operation			
				05
• APPLI		pin 1, Gate		
-	ide switching t regulators	1 2 3 2, Drain 3, Source		
	atic test equipment			TO-220C packag
, laterna				
• ABSOI	LUTE MAXIMUM RATINGS(Ta=25°C	;)		F T
SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>DSS</sub>	Drain-Source Voltage	-65	V	
$V_{GS}$	Gate-Source Voltage	±15	v	K T T T
				+
ID	Drain Current-Continuous	-28	A	
I <sub>DM</sub>	Drain Current-Single Pulsed	-90	Α	
PD	Total Dissipation @Tc=25°C	83	w	DIM MIN MAX
	Operating Junction Temperature	EE. 1E0	°C	A 15.50 15.90 B 9.90 10.20
Tj	Operating Junction Temperature	-55~150	C C	C 4.20 4.50 D 0.70 0.90
T <sub>stg</sub>	Storage Temperature	-55~150	°C	F 3.40 3.70 G 4.98 5.18
				H 2.68 2.90
• THERM	MAL CHARACTERISTICS			J 0.44 0.60 K 13.00 13.40
				L 1.10 1.45 Q 2.70 2.90
CVMDOI	DADAMETED		LINUT	D 2 20 2 70

SYMBOL PARAMETER		MAX	UNIT	
R <sub>th(j-c)</sub>	Channel-to-case thermal resistance	1.5	°C/W	



6.45 8.66

U V

6.65 8.86



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#### **ELECTRICAL CHARACTERISTICS**

#### $T_{\text{c}}\text{=}25^{\circ}\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT	
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; I <sub>D</sub> = -250 μ A	-65			V	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> ; I <sub>D</sub> = -250 μ A	-2.5		-4.5	V	
$R_{DS(on)}$	Drain-Source On-Resistance	V <sub>GS</sub> = -10V; I <sub>D</sub> = -14A			45	mΩ	
lgss	Gate-Source Leakage Current	V <sub>GS</sub> = ±15V; V <sub>DS</sub> =0			±50	nA	
Idds	Drain-Source Leakage Current	V <sub>DS</sub> = V <sub>DSS</sub> ; V <sub>GS</sub> = 0V			-3	- μ <b>Α</b>	
		V <sub>DS</sub> = V <sub>DSS</sub> ; V <sub>GS</sub> = 0V; T <sub>J</sub> =125°C			-100		
$V_{\text{SD}}$	Diode forward voltage	I <sub>F</sub> = -28A; V <sub>GS</sub> = 0V			-1.5	V	

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